NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE40H21 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

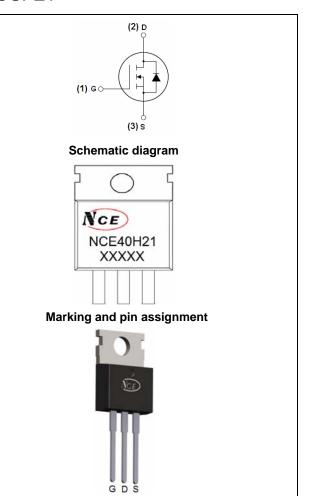
- $V_{DS} = 40V$, $I_{D} = 210A$ $R_{DS(ON)} < 3.2 m\Omega$ @ $V_{GS} = 10V$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



TO-220-3L top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| NCE40H21 | NCE40H21 | TO-220-3L | - | - | - |

Absolute Maximum Ratings (T_A=25 °Cunless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|------------------------|
| Drain-Source Voltage | V _{DS} | 40 | V |
| Gate-Source Voltage | V _G S | ±20 | V |
| Drain Current-Continuous | I _D | 210 | Α |
| Drain Current-Continuous(T _C =100 °C) | I _D (100℃) | 148 | А |
| Pulsed Drain Current | I _{DM} | 840 | А |
| Maximum Power Dissipation | P _D | 310 | W |
| Derating factor | | 2.07 | W/℃ |
| Single pulse avalanche energy (Note 5) | E _{AS} | 2500 | mJ |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 175 | $^{\circ}\!\mathbb{C}$ |



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NCE40H21

Thermal Characteristic

| Thermal Resistance, Junction-to-Case (Note 2) | R _{eJC} | 0.48 | °C/W | 1 |
|---|------------------|------|------|---|
|---|------------------|------|------|---|

Electrical Characteristics (T_A=25°C unless otherwise noted)

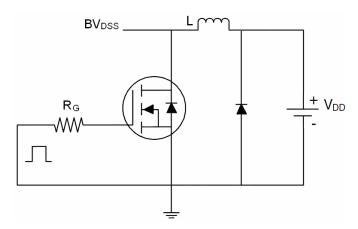
| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|--|-----|-------|----------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 40 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =40V,V _{GS} =0V | - | - | 1 | μΑ |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 1.3 | 1.8 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 2.3 | 3.2 | mΩ |
| Forward Transconductance | g FS | V _{DS} =5V,I _D =20A | - | 100 | - | S |
| Dynamic Characteristics (Note4) | | | | | | |
| Input Capacitance | C _{lss} | \/ -05\/\/ -0\/ | - | 10331 | - | PF |
| Output Capacitance | C _{oss} | $V_{DS}=25V,V_{GS}=0V,$ | - | 1160 | - | PF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 1045 | - | PF |
| Switching Characteristics (Note 4) | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 41 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =30 V , R_L =15 Ω , | - | 40 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | R_G =2.5 Ω , V_{GS} =10 V | - | 145 | - | nS |
| Turn-Off Fall Time | t _f | | - | 65 | - | nS |
| Total Gate Charge | Qg | | - | 239 | - | nC |
| Gate-Source Charge | Q _{gs} | I _D =20A,V _{DD} =20V,V _{GS} =10V | - | 23.5 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 49.6 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage (Note 3) | V_{SD} | V _{GS} =0V,I _S =20A | - | 0.85 | 1.2 | V |
| Diode Forward Current (Note 2) | Is | | - | - | 210 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 20A | - | 55 | | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs ^(Note3) | - | 90 | | nC |
| Forward Turn-On Time | t _{on} | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | y LS+LD) | |
| | | | | | | |

Notes:

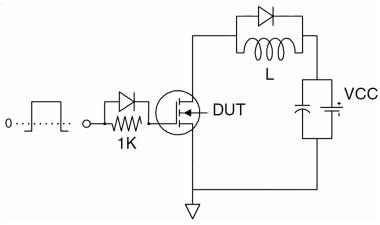
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25 Ω

Test circuit

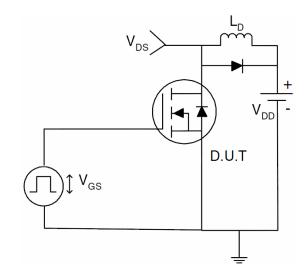
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:



Typical Electrical and Thermal Characteristics (Curves)

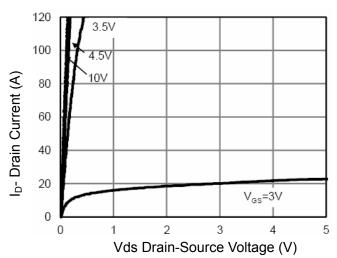


Figure 1 Output Characteristics

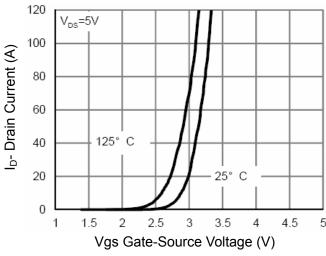


Figure 2 Transfer Characteristics

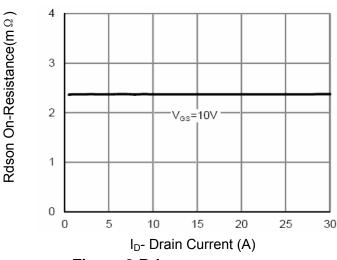


Figure 3 Rdson- Drain Current

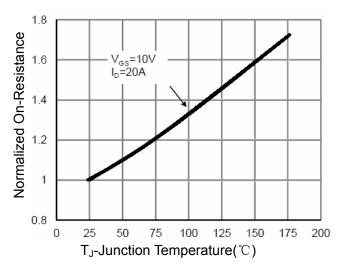


Figure 4 Rdson-JunctionTemperature

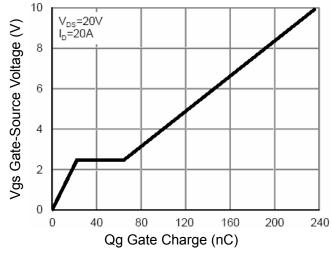


Figure 5 Gate Charge

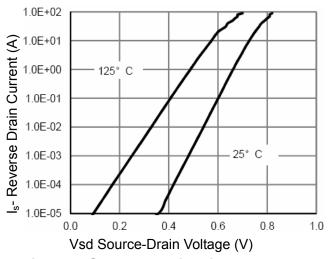


Figure 6 Source- Drain Diode Forward



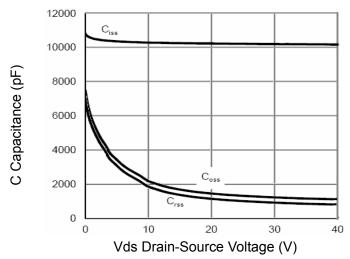


Figure 7 Capacitance vs Vds

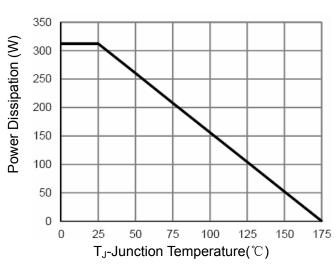


Figure 9 Power De-rating

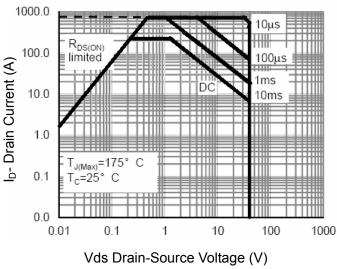


Figure 8 Safe Operation Area

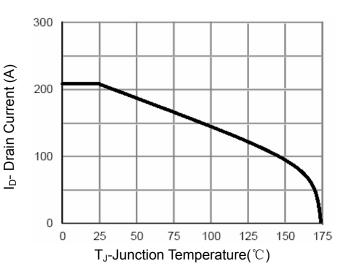
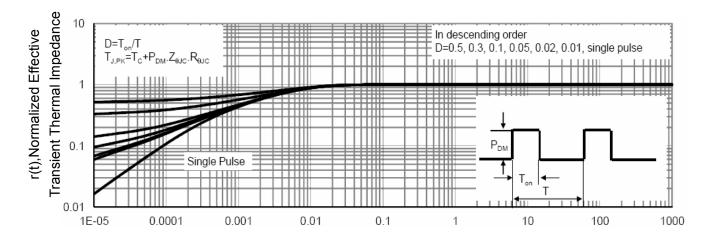


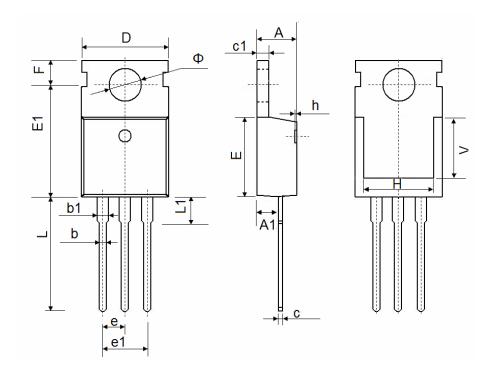
Figure 10 Current De-rating



Square Wave Pluse Duration (sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



| Symbol | Dimensions I | n Millimeters | Dimensions In Inches | | |
|--------|--------------|-----------------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| Α | 4.400 | 4.600 | 0.173 | 0.181 | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| С | 0.330 | 0.650 | 0.013 | 0.026 | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| D | 9.910 | 10.250 | 0.390 | 0.404 | |
| Е | 8.9500 | 9.750 | 0.352 | 0.384 | |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 | |
| е | 2.540 | TYP. | 0.100 | TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| F | 2.650 | 2.950 | 0.104 | 0.116 | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| L | 12.900 | 13.400 | 0.508 | 0.528 | |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 | |
| V | 7.500 | 7.500 REF. 0.295 REF. | | REF. | |
| Ф | 3.400 | 3.800 | 0.134 | 0.150 | |



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